

RESEARCH ARTICLE

Ab initio study of anisotropic mechanical and electronic properties of strained carbon-nitride nanosheet with interlayer bonding

Hao Cheng^{1,2}, Jin-Cheng Zheng^{1,2,†}

¹Department of Physics and the Collaborative Innovation Center for Optoelectronic Semiconductors and Efficient Devices, Xiamen University, Xiamen 361005, China

²Department of Physics, Xiamen University Malaysia, 439000, Sepang, Selangor, Malaysia

Corresponding author. E-mail: [†]jczheng@xmu.edu.cn

SUPPLEMENTARY MATERIAL

Table 1 The calculated structure parameters of CN nanosheet in LB (low-buckled) geometry without interlayer bonding and planar (PL) geometry. The values of angle between intralayer bond C-N-C (α), C-N bond length (d_{CN}), lattice constant (a), and cohesive energy (E_{coh}) are given.

Structure	α ($^{\circ}$)	d_{CN} (\AA)	a (\AA)	E_{coh} (eV/atom)
LB geometry without interlayer bonding	119.1	1.390	2.396	7.994
Planar geometry	120.0	1.385	2.399	7.992

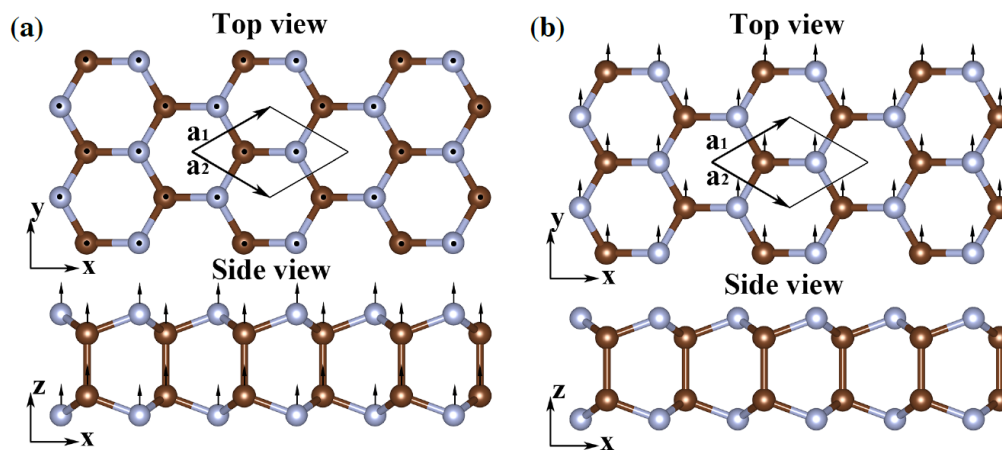


Fig. 1 The illustration of unstable eigenvector corresponding to (a) out-of-plane transverse phonon branch ZA at $\epsilon_{xx} = 0.13$ and (b) in-plane transverse phonon branch TA at $\epsilon_{yy} = 0.18$.

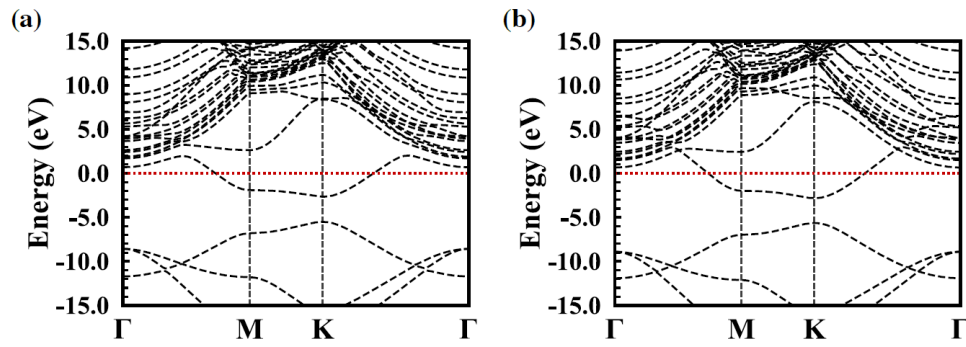


Fig. 2 Calculated electronic band structures of CN nanosheet in (a) LB geometry without interlayer bonding and (b) planar (PL) geometry are presented. The Fermi energy is set to be zero.